

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

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Please amend paragraph [0005] on page 2 of the Specification as follows:

According to one aspect of the present invention, there is provided a producing method of a semiconductor device, ~~characterized by~~ comprising:

a film thinning ~~step of thinning~~ a silicon oxide film by heating the silicon oxide film formed after a surface of a silicon substrate is etched by chemical liquid, and

a one of thermal oxidizing ~~step of~~ by heating the thinned silicon oxide film to oxidize the silicon oxide film by gas including at least oxygen, ~~or a~~ and plasma oxidizing ~~step of oxidizing~~ the thinned silicon oxide film by plasma discharged gas including at least oxygen.

Please amend paragraph [0007] on page 4 of the Specification as follows:

According to a preferable aspect of the present invention, there is provided a producing method of a semiconductor device, ~~characterized by~~ comprising:

a film thinning ~~step of thinning~~ a silicon oxide film by heating the silicon oxide film formed after a surface of a silicon substrate is etched by chemical liquid, and

a one of thermal oxidizing ~~step of~~ by heating the thinned silicon oxide film to oxidize the silicon oxide film by gas including at least oxygen, ~~or a~~ and plasma oxidizing ~~step of oxidizing~~ the thinned silicon oxide film by plasma discharged gas including at least oxygen.